

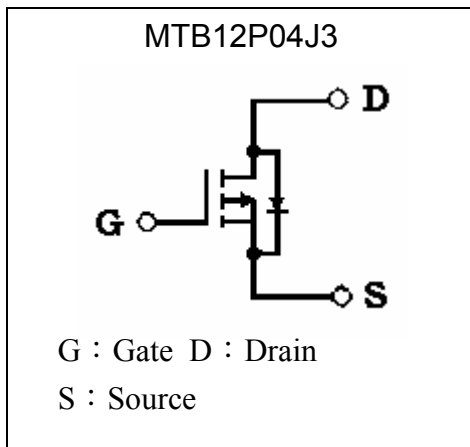
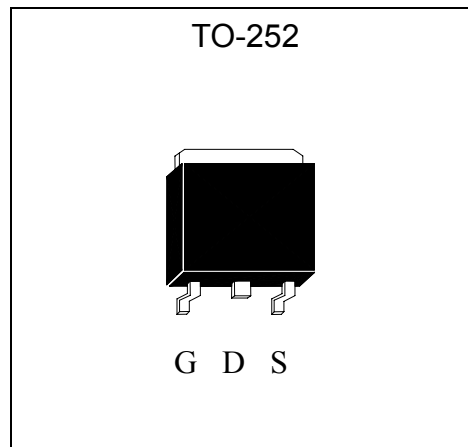
P-Channel Logic Level Enhancement Mode Power MOSFET

MTB12P04J3

BV_{DSS}	-40V
I_D	-25A
$R_{DS(on)(MAX)}$	12.6m Ω

Features

- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating & Halogen-free package

Equivalent Circuit

Outline

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current @ $T_C=25^\circ\text{C}$	I_D	-25	A
Continuous Drain Current @ $T_C=100^\circ\text{C}$	I_D	-18	
Pulsed Drain Current *1	I_{DM}	-100	
Avalanche Current	I_{AS}	-25	
Avalanche Energy @ $L=0.1\text{mH}$, $I_D=-25\text{A}$, $R_G=25\Omega$	E_{AS}	31.25	mJ
Repetitive Avalanche Energy @ $L=0.05\text{mH}$ *2	E_{AR}	15	
Total Power Dissipation @ $T_C=25^\circ\text{C}$	P_d	50	W
Total Power Dissipation @ $T_C=100^\circ\text{C}$		17	
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+175	$^\circ\text{C}$

Note : *1. Pulse width limited by maximum junction temperature

 *2. Duty cycle $\leq 1\%$



Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{th,j-a}	75	°C/W

Characteristics (T_c=25°C, unless otherwise specified)

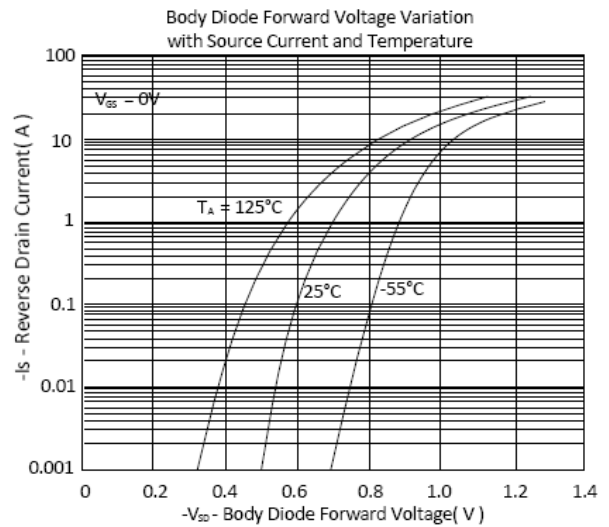
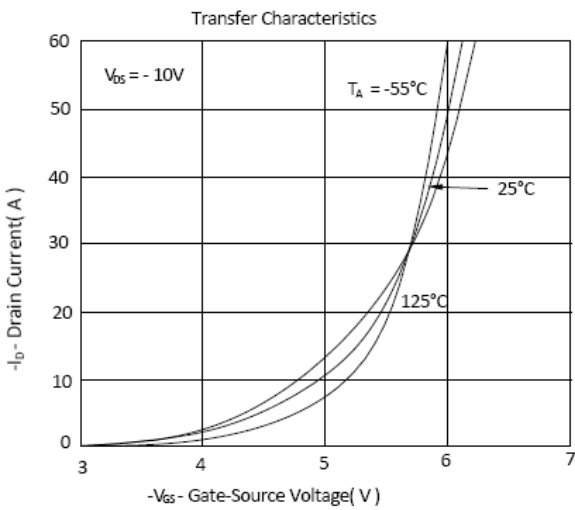
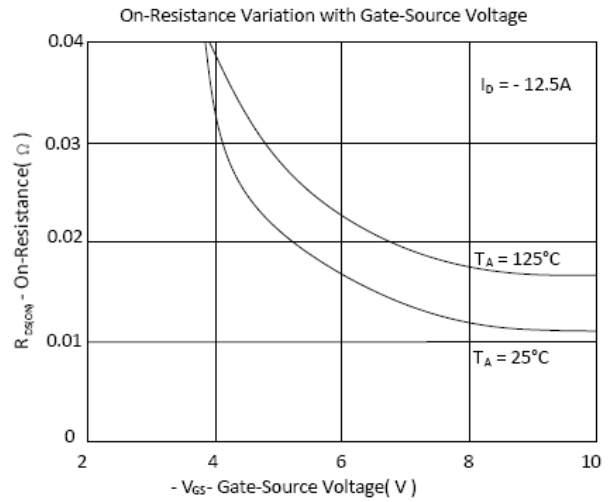
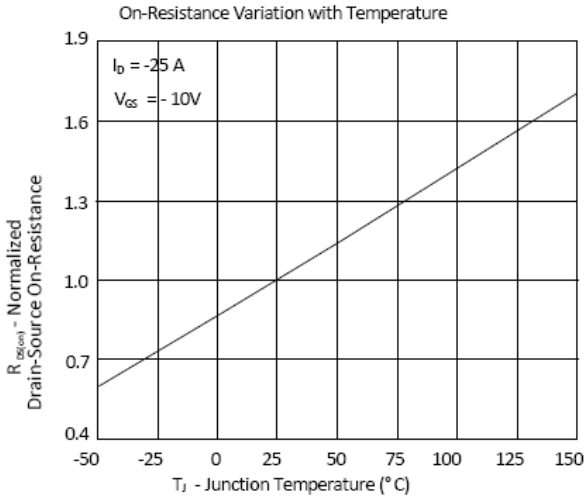
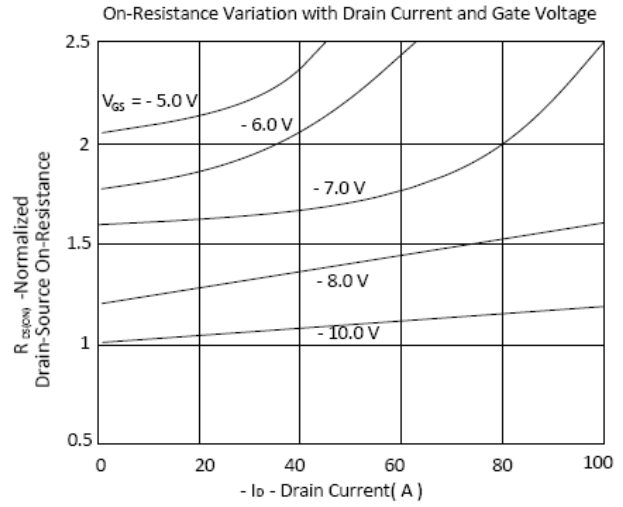
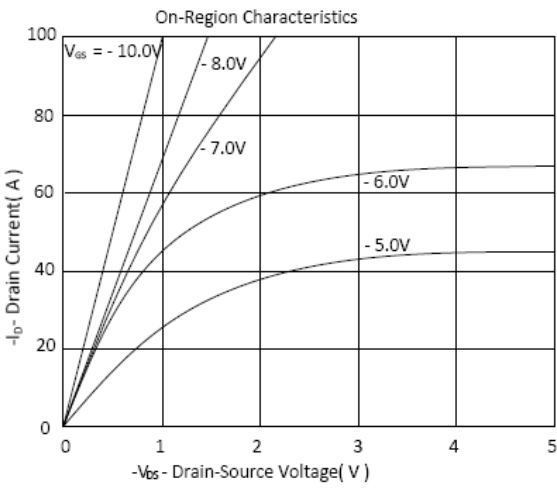
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
B _V DSS	-40	-	-	V	V _{GS} =0, I _D =-250μA
V _{GS(th)}	-1.0	-1.8	-3.2	V	V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20, V _{DS} =0
I _{DSS}	-	-	-1	μA	V _{DS} =-32V, V _{GS} =0
	-	-	-25	μA	V _{DS} =-30V, V _{GS} =0, T _J =125°C
I _{D(ON)} *1	-25	-	-	A	V _{DS} =-5V, V _{GS} =-4.5V
R _{DS(ON)} *1	-	11.3	12.6	mΩ	V _{GS} =-10V, I _D =-25A
	-	18	23	mΩ	V _{GS} =-5V, I _D =-20A
G _{FS} *1	-	28	-	S	V _{DS} =-5V, I _D =-25A
Dynamic					
Q _g *1, 2	-	50	-	nC	I _D =-25A, V _{DS} =-20V, V _{GS} =-10V
Q _{gs} *1, 2	-	8	-		
Q _{gd} *1, 2	-	11	-		
t _{d(ON)} *1, 2	-	15	-	ns	V _{DS} =-20V, I _D =-1A, V _{GS} =-10V, R _G =6Ω
t _r *1, 2	-	40	-		
t _{d(OFF)} *1, 2	-	60	-		
t _f *1, 2	-	50	-		
C _{iss}	-	3925	-	pF	V _{GS} =0V, V _{DS} =-20V, f=1MHz
C _{oss}	-	1330	-		
C _{rss}	-	1162	-		
R _g	-	3.5	-	Ω	V _{GS} =15mV, V _{DS} =0, f=1MHz
Source-Drain Diode					
I _S *1	-	-	-25	A	
I _{SM} *3	-	-	-100		
V _{SD} *1	-	-	-1.3	V	I _F =I _S , V _{GS} =0V
t _{rr}	-	40	-	ns	I _F =-25A, dI _F /dt=100A/μs
Q _{rr}	-	30	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

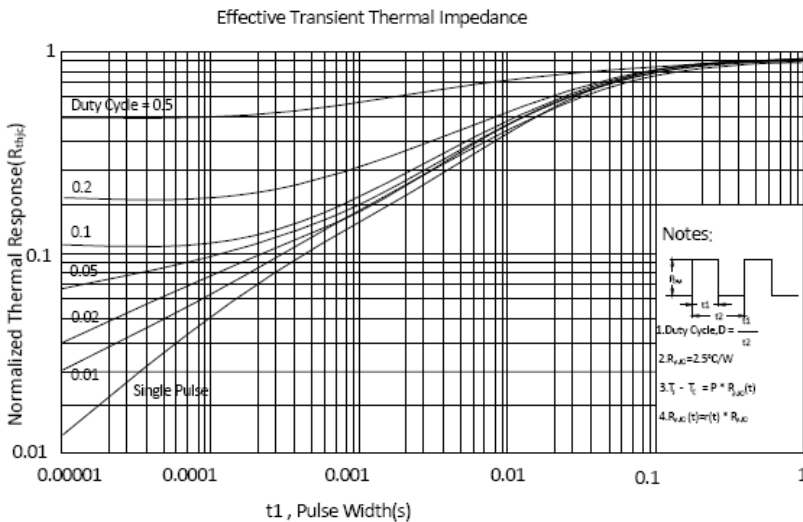
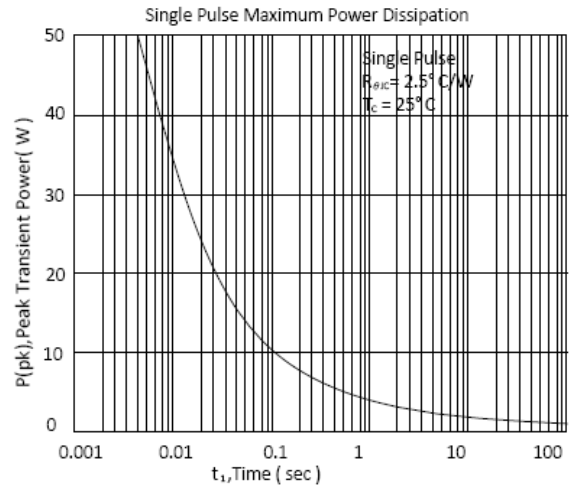
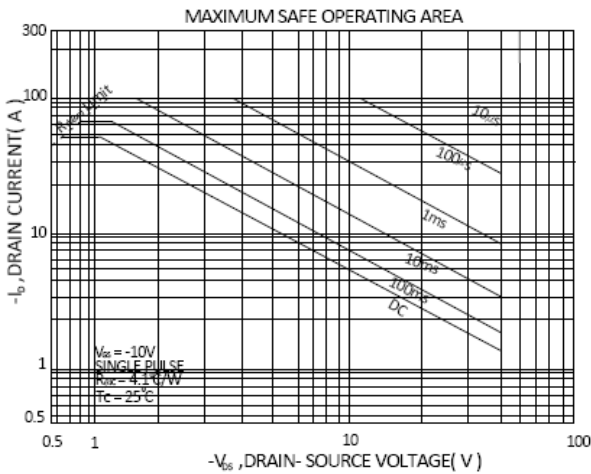
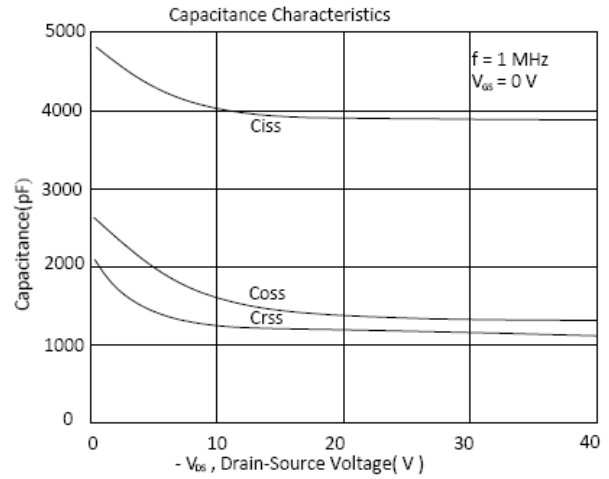
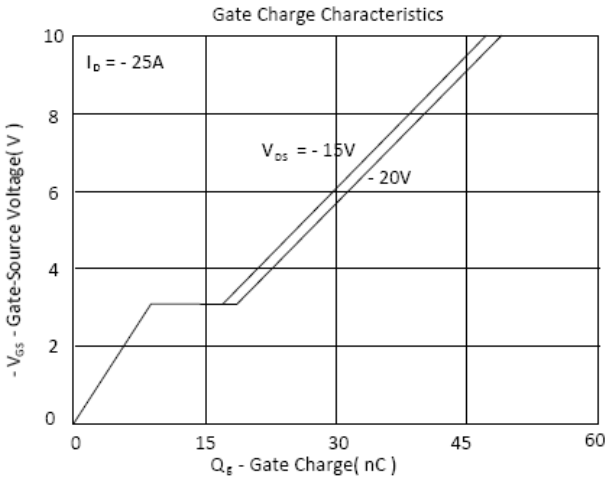
Ordering Information

Device	Package	Shipping	Marking
MTB12P04J3	TO-252 (Pb-free lead plating & Halogen-free package)	2500 pcs / Tape & Reel	B12P04

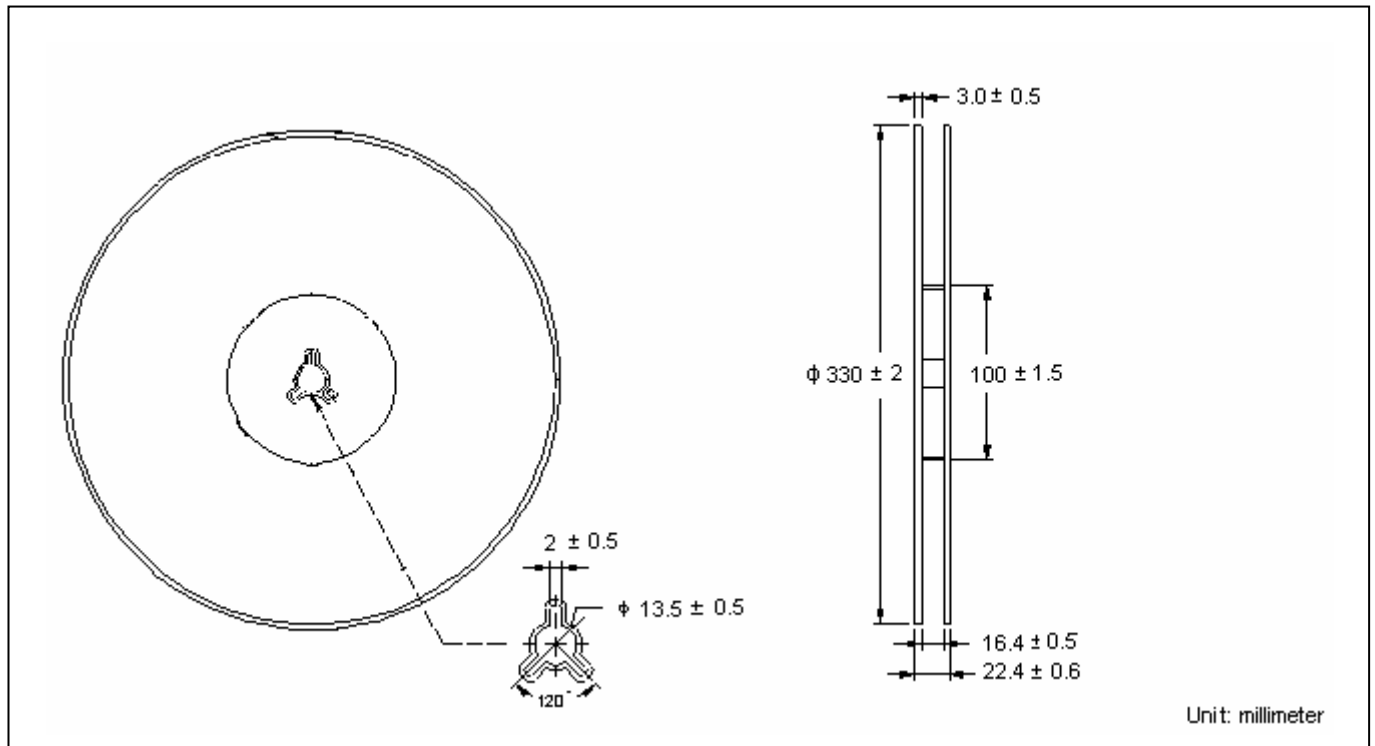
Characteristic Curves



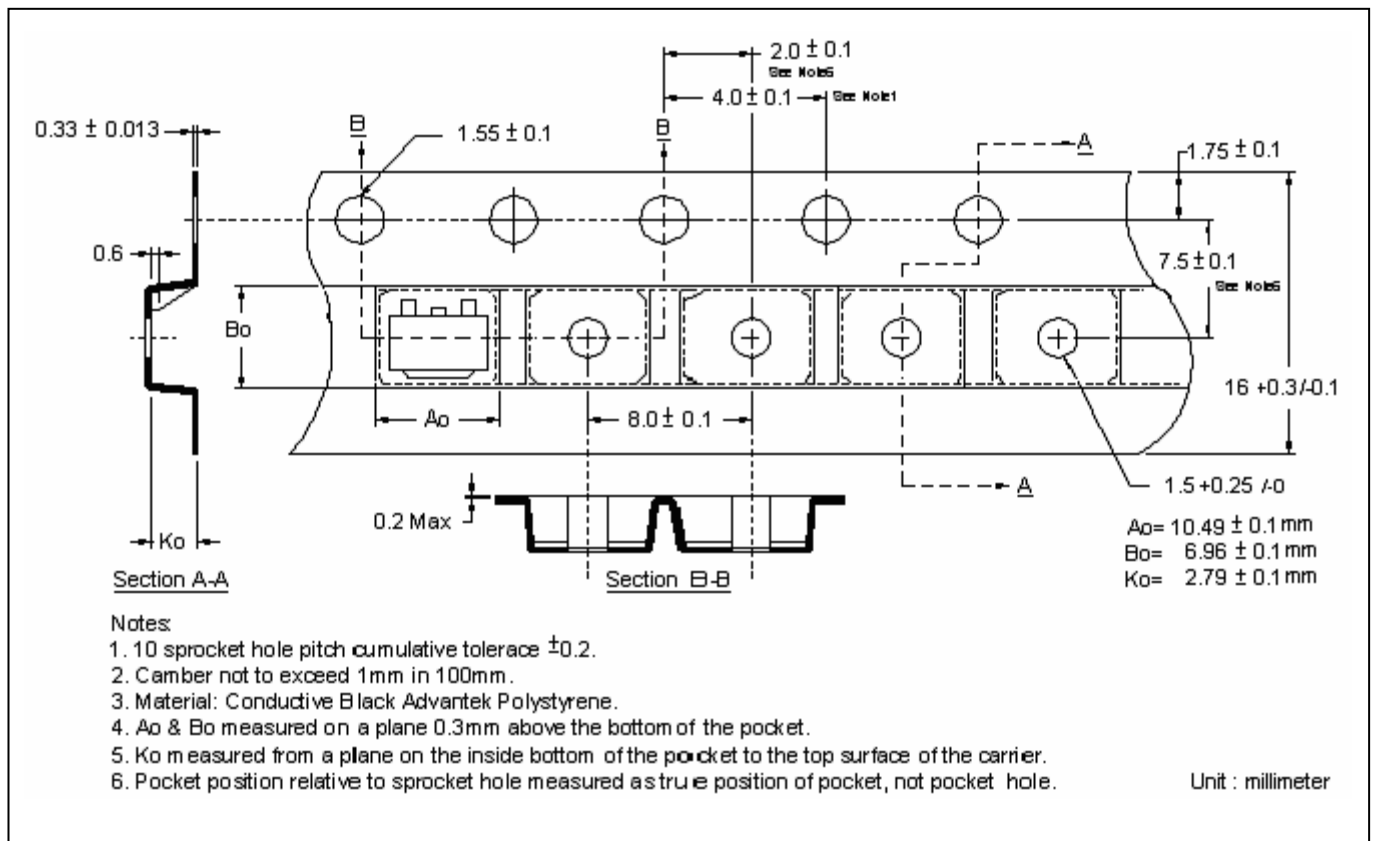
Characteristic Curves(Cont.)



Reel Dimension



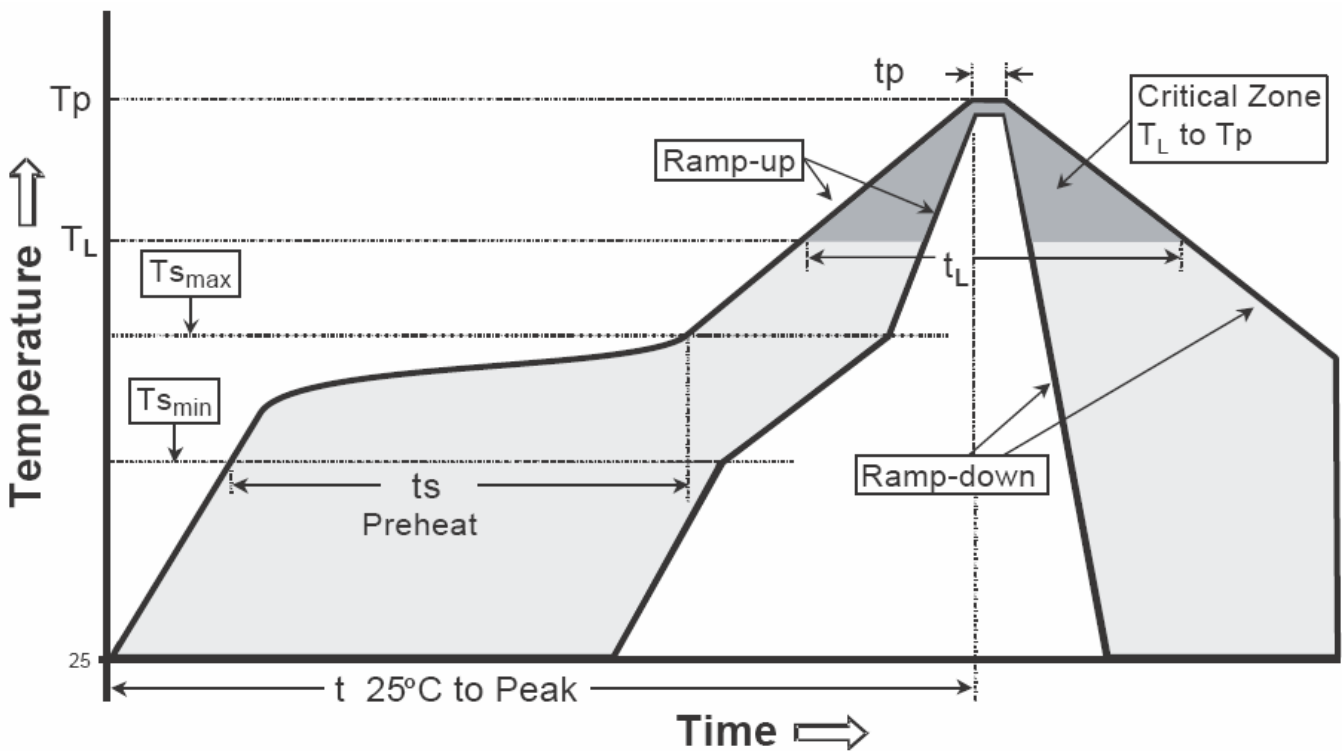
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

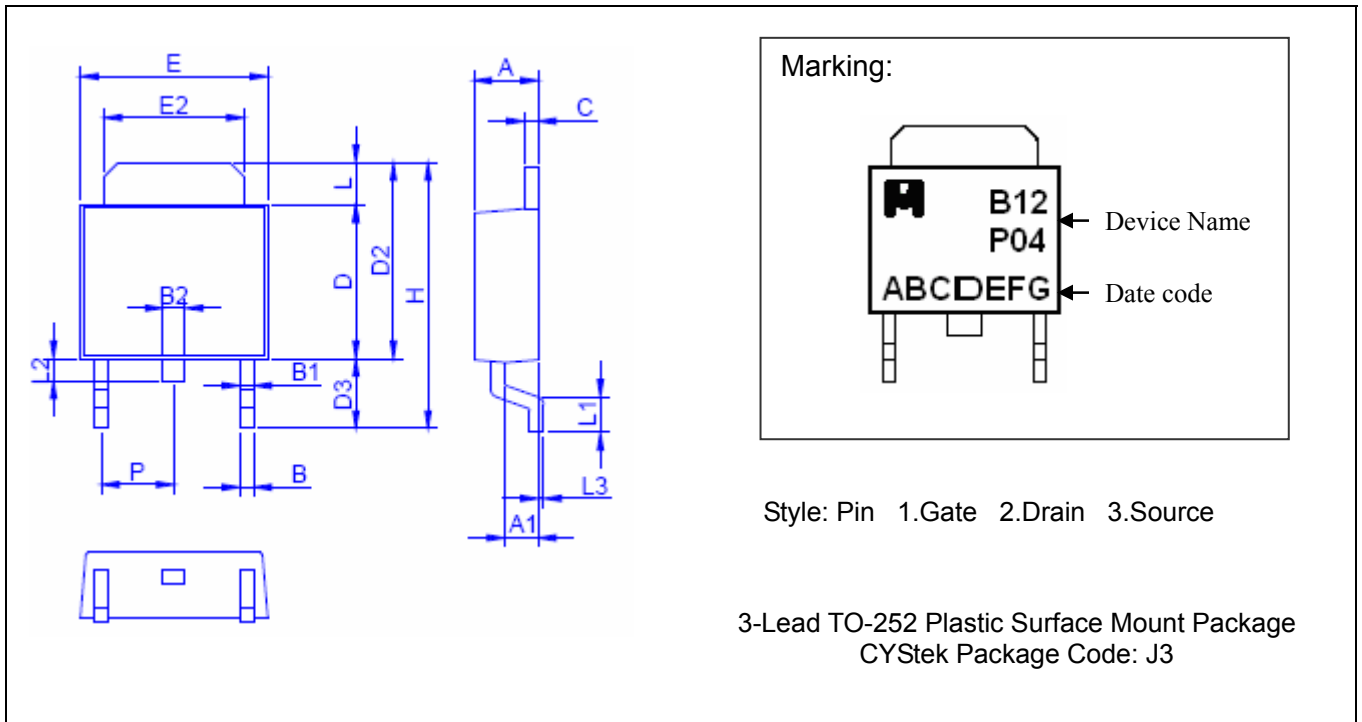
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



Marking:

Style: Pin 1.Gate 2.Drain 3.Source

3-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J3

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0827	0.0984	2.10	2.50	E	0.2520	0.2638	6.40	6.70
A1	0.0374	0.0512	0.95	1.30	E2	0.1890	0.2146	4.80	5.45
B	0.0118	0.0335	0.30	0.85	H	0.3622	0.3996	9.20	10.15
B1	0.0157	0.0370	0.40	0.94	L	0.0350	0.0669	0.89	1.70
B2	0.0236	0.0394	0.60	1.00	L1	0.0354	0.0650	0.90	1.65
C	0.0157	0.0236	0.40	0.60	L2	0.0197	0.0433	0.50	1.10
D	0.2087	0.2441	5.30	6.20	L3	0.0000	0.0118	0.00	0.30
D2	0.2638	0.2874	6.70	7.30	P	0.0827	0.0984	2.10	2.50
D3	0.0866	0.1181	2.20	3.00					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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